

# FQPF19N20

# N-Channel QFET<sup>®</sup> MOSFET 200 V, 11.8 A, 150 m $\Omega$

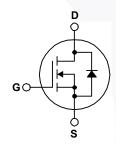
### **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### **Features**

- 11.8 A, 200 V,  $R_{DS(on)}$  = 150 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 5.9 A
- Low Gate Charge (Typ. 31 nC)
- · Low Crss (Typ. 30 pF)
- · 100% Avalanche Tested





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQPF19N20	Unit	
$V_{DSS}$	Drain-Source Voltage		200	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		11.8	Α	
	- Continuous (T <sub>C</sub> = 100°C	)	7.5	Α	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	48	Α	
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	250	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	11.8	Α	
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	5.0	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns	
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C		50	W	
			0.4	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C	

### **Thermal Characteristics**

Symbol	Parameter	FQPF19N20	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.5	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF19N20	FQPF19N20	TO-220F	Tube	N/A	N/A	50 units

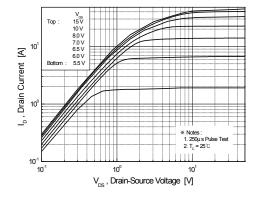
## **Electrical Characteristics**

T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	200			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°0	C	0.18		V/°C
I <sub>DSS</sub>	Zero Cata Valta sa Duain Cumant	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 160 V, T <sub>C</sub> = 125°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V	_		100	nΑ
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5.9 A		0.12	0.15	Ω
g <sub>FS</sub>	Forward Transconductance	v <sub>DS</sub> = 40 V, I <sub>D</sub> = 5.9 A		8.7		S
Dynam C <sub>iss</sub>	ic Characteristics Input Capacitance	V - 25 V V - 2 V		1220	1600	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		220	290	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1.0 MHz		30	40	pF
						P.
	ing Characteristics		-			
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 100 V, I <sub>D</sub> = 19.4 A,		20	50	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		190	390	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	(Note		55	120	ns
t <sub>f</sub>	Turn-Off Fall Time			80	170	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 160 V, I <sub>D</sub> = 19.4 A,		31	40	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		8.6		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note	4)	13.5		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				11.8	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				48	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage V <sub>GS</sub> = 0 V, I <sub>S</sub> = 11.8 A				1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 19.4 A,		140		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs		0.69		μС

- Notes: 
  1. Repetitive Rating : Pulse width limited by maximum junction temperature. 
  2. L = 2.7 mH,  $I_{AB}$  = 11.8 A,  $V_{DD}$  = 50 V,  $R_{G}$  = 25  $\Omega$ , starting  $T_{J}$  = 25°C. 
  3.  $I_{SD}$   $\leq$  19.4 A, di/dt  $\leq$  300 A/ $\mu$ s,  $V_{DD}$   $\leq$  BV $_{DSS}$ , starting  $T_{J}$  = 25°C. 
  4. Essentially independent of operating temperature.

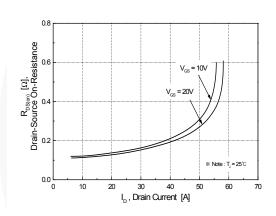
# **Typical Characteristics**



W 10<sup>1</sup> 25°C -55°C -55°C

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



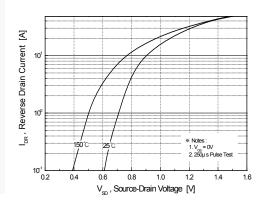
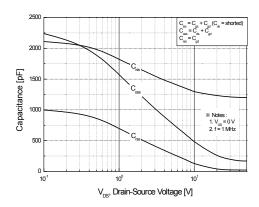


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



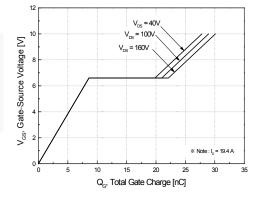
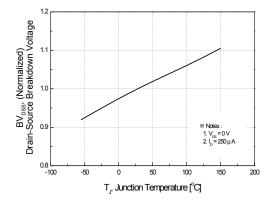


Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

# Typical Characteristics (continued)



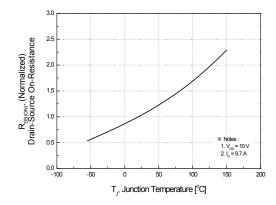
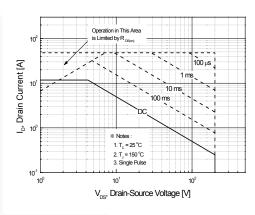


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



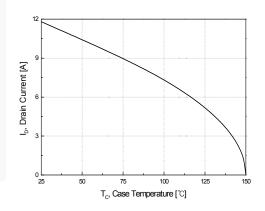


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

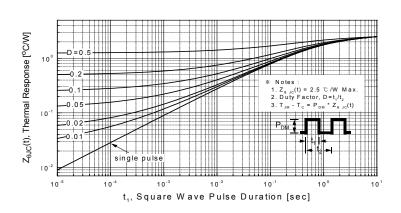


Figure 11. Transient Thermal Response Curve

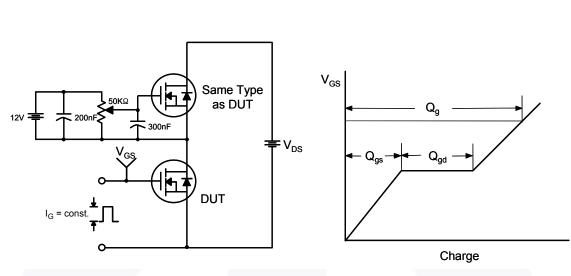


Figure 12. Gate Charge Test Circuit & Waveform

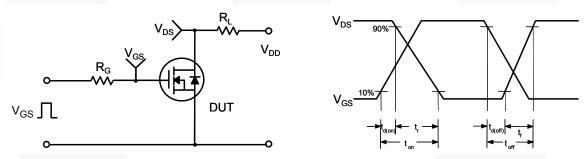


Figure 13. Resistive Switching Test Circuit & Waveforms

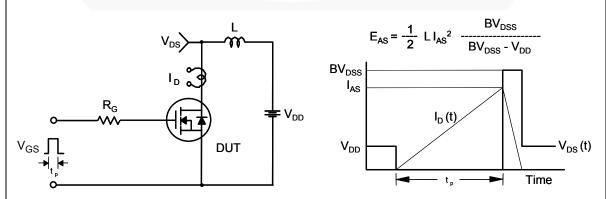
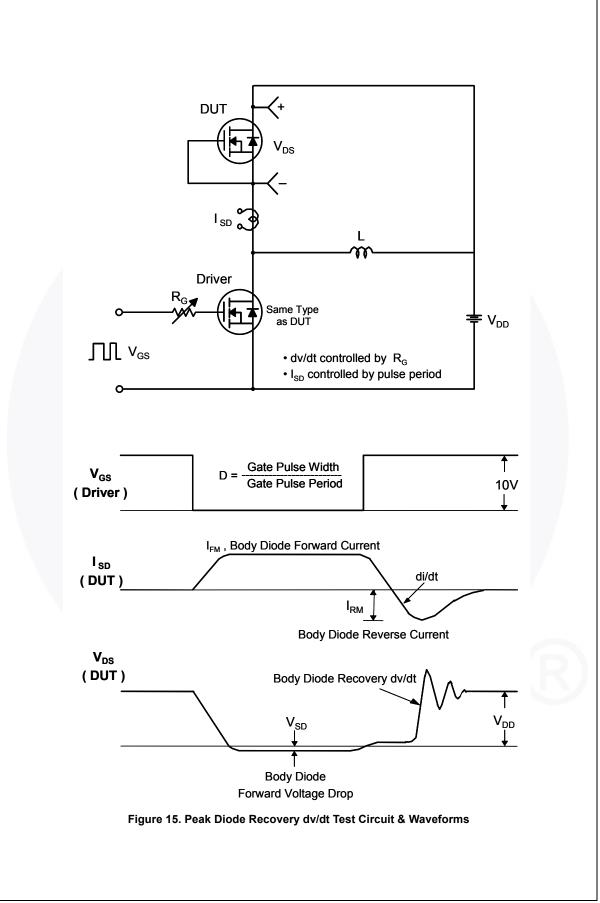


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



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# **Mechanical Dimensions**

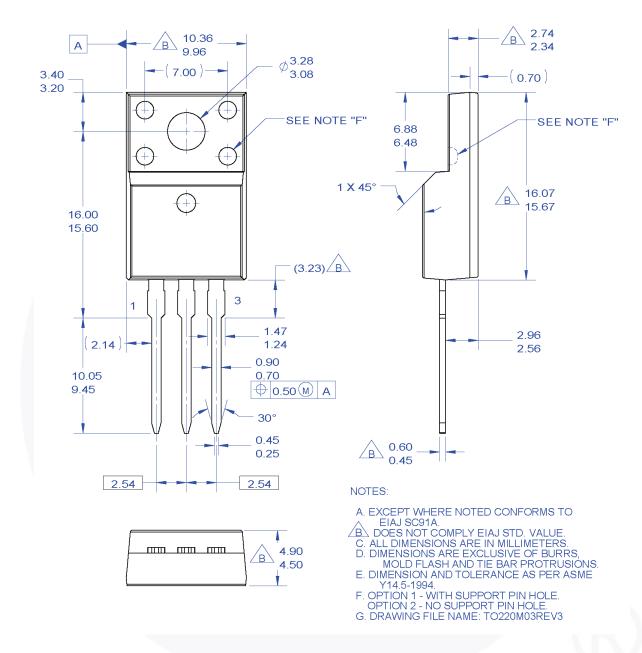


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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